

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC2703

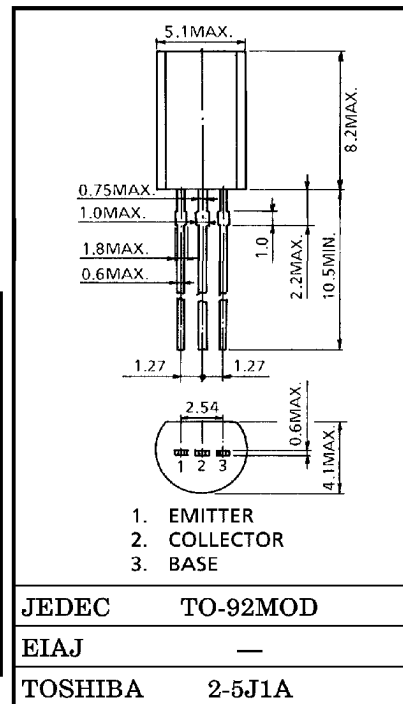
AUDIO POWER AMPLIFIER APPLICATIONS.

Unit in mm

- High DC Current Gain : $h_{FE} = 100 \sim 320$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	30	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	1	A
Base Current	I _B	0.1	A
Collector Power Dissipation	P _C	900	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} = 30V, I _E = 0	—	—	100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 5V, I _C = 0	—	—	100	nA
Collector-Emitter Breakdown Voltage	V _{(BR) CEO}	I _C = 10mA, I _B = 0	30	—	—	V
DC Current Gain	h _{FE} (1) (Note)	V _{CE} = 2V, I _C = 100mA	100	—	320	
	h _{FE} (2)	V _{CE} = 2V, I _C = 800mA	40	—	—	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C = 800mA, I _B = 80mA	—	—	0.5	V
Base-Emitter Voltage	V _{BE}	V _{CE} = 2V, I _C = 800mA	—	0.9	1.5	V
Transition Frequency	f _T	V _{CE} = 2V, I _C = 100mA	—	150	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	13	—	pF

Note : h_{FE} (1) Classification O : 100~200, Y : 160~320

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